

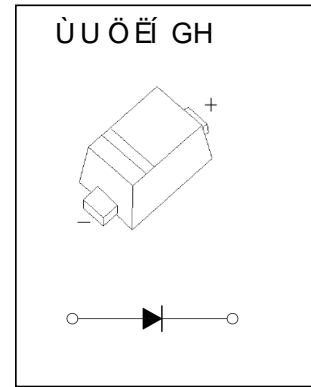
# GENERAL PURPOSE PIN DIODES

**FEATURES**

- Low diode capacitance
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**MARKING: A5**

Low diode forward resistance


**Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C**

Parameter	Symbol	Limits	Unit
Continuous reverse voltage	V <sub>R</sub>	60	V
Continuous Forward Current	I <sub>F</sub>	50	mA
Power Dissipation (T <sub>A</sub> =90°C)	P <sub>d</sub>	715	mW
Thermal Resistance from Junction to soldering point	R <sub>θJS</sub>	85	°C/W
Junction temperature	T <sub>j</sub>	-65~+150	°C
Storage temperature	T <sub>STG</sub>	-65~+150	°C

**Electrical Ratings @T<sub>A</sub>=25°C**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Continuous reverse voltage	V <sub>R</sub>	50			V	I <sub>R</sub> =10μA
Forward voltage	V <sub>F</sub>			1.1	V	I <sub>F</sub> =50mA
Reverse current	I <sub>R</sub>			100	nA	V <sub>R</sub> =50V
Diode capacitance	C <sub>d1</sub>		0.4*		pF	V <sub>R</sub> =0V, f=1MHz
	C <sub>d2</sub>			0.55	pF	V <sub>R</sub> =1V, f=1MHz
	C <sub>d3</sub>			0.35	pF	V <sub>R</sub> =5V, f=1MHz
Diode forward resistance	r <sub>D</sub>			9	Ω	I <sub>F</sub> =0.5mA, f=100MHz; note1
	r <sub>D</sub>			6.5	Ω	I <sub>F</sub> =1mA, f=100MHz; note1
	r <sub>D</sub>			2.5	Ω	I <sub>F</sub> =10mA, f=100MHz; note1

Note 1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

